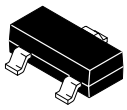
MOSFET – Power, Single, N-Channel, SOT-23, 2.4 x 2.9 x 1.0 mm

20 V, 3.6 A

NTR3C21NZ

$V_{(BR)DSS}$	$R_{DS(on)}$ Max	I_D MAX
20 V	24 mΩ @ 4.5 V	3.6 A
	26 mΩ @ 3.7 V	
	29 mΩ @ 3.3 V	
	33 mΩ @ 2.5 V	
	55 mΩ @ 1.8 V	



SOT−23
CASE 318
STYLE 21

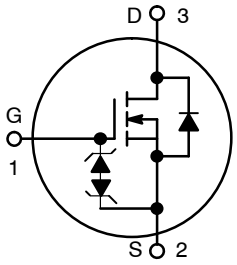
Features

- Advanced Trench Technology
- Ultra−Low $R_{DS(on)}$ in SOT−23 Package
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Power Load Switch
- Power Management

N−Channel MOSFET



MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Symbol	Parameter			Value	Unit
V_{DSS}	Drain−to−Source Voltage			20	V
V_{GS}	Gate−to−Source Voltage			±8	V
I_D	Continuous Drain Current (Note 1)	Steady State	T_A = 25°C	3.6	A
			T_A = 85°C	2.6	
		t ≤ 5 s	T_A = 25°C	6.5	
P_D	Power Dissipation (Note 1)	Steady State	T_A = 25°C	0.47	W
		t ≤ 5 s		1.56	
I_{DM}	Pulsed Drain Current	t_p = 10 μs		13.2	A
T_J, T_{STG}	Operating Junction and Storage Temperature			−55 to 150	°C
I_S	Source Current (Body Diode) (Note 2)			2.2	A
T_L	Lead Temperature for Soldering Purposes (1/8 in from case for 10 s)			260	°C

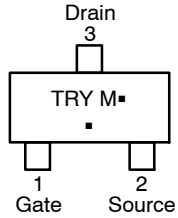
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Junction−to−Ambient – Steady State (Note 1)	264	°C/W
$R_{\theta JA}$	Junction−to−Ambient – t ≤ 5 s (Note 1)	80	

1. Surface−mounted on FR4 board using 1 in sq. pad size (Cu area = 1.127 in sq. [1 oz] including traces).
2. Pulse Test: pulse width ≤ 300 ms, duty cycle ≤ 2%.

MARKING DIAGRAM & PIN ASSIGNMENT



TRY = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note AND8002/D.

ORDERING INFORMATION

Device	Package	Shipping†
NTR3C21NZT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
NTR3C21NZT3G	SOT−23 (Pb−Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
$V_{(BR)DSS}$	Drain−to−Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA		20			V
$V_{(BR)DSS}/T_J$	Drain−to−Source Breakdown Voltage Temperature Coefficient	I_D = 250 μA, ref to 25°C			21.6		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0 V, V_{DS} = 20 V	T_J = 25°C			1.0	μA
			T_J = 85°C			5.0	μA
I_{GSS}	Gate−to−Source Leakage Current	V_{DS} = 0 V, V_{GS} = ±8 V				±10	μA
ON CHARACTERISTICS (Note 3)							
$V_{GS(TH)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA		0.45		1.0	V
$V_{GS(TH)}/T_J$	Negative Threshold Temperature Coefficient				2.7		mV/°C
$R_{DS(on)}$	Drain−to−Source On Resistance	V_{GS} = 4.5 V	I_D = 5 A		18	24	mΩ
		V_{GS} = 3.7 V	I_D = 4 A		18.5	26	
		V_{GS} = 3.3 V	I_D = 3 A		19	29	
		V_{GS} = 2.5 V	I_D = 2 A		20	33	
		V_{GS} = 1.8 V	I_D = 1 A		25	55	
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 3 A			20		S
CHARGES AND CAPACITANCES							
C_{iss}	Input Capacitance	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = 16 V			1540		pF
C_{oss}	Output Capacitance				105		
C_{rss}	Reverse Transfer Capacitance				86		
$Q_{G(TOT)}$	Total Gate Charge	V_{GS} = 4.5 V, V_{DS} = 16 V, I_D = 5 A			17.8		nC
$Q_{G(TH)}$	Threshold Gate Charge				2.1		
Q_{GS}	Gate−to−Source Charge				3.0		
Q_{GD}	Gate−to−Drain Charge				0.8		
SWITCHING CHARACTERISTICS (Note 4)							
$t_{d(on)}$	Turn−On Delay Time	V_{GS} = 4.5 V, V_{DS} = 16 V, I_D = 5 A, R_G = 6.0 Ω			7.0		ns
t_r	Rise Time				14		
$t_{d(off)}$	Turn−Off Delay Time				420		
t_f	Fall Time				4670		
DRAIN−SOURCE DIODE CHARACTERISTICS							
V_{SD}	Forward Diode Voltage	V_{GS} = 0 V, I_S = 2.0 A	T_J = 25°C		0.7	1.0	V
			T_J = 125°C		0.56		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: pulse width ≤ 300 ms, duty cycle ≤ 2%.
4. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

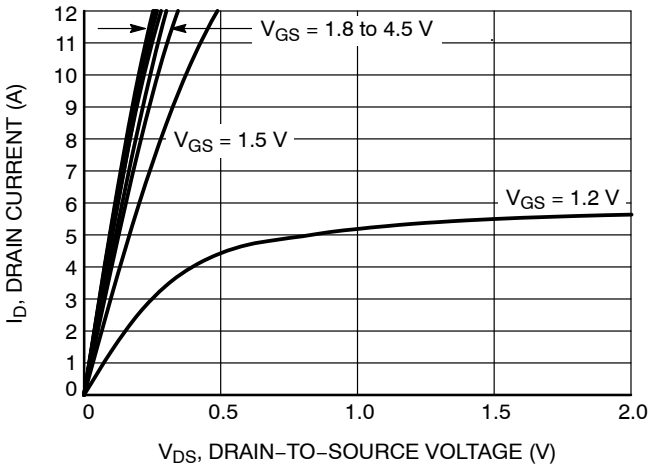


Figure 1. On−Region Characteristics

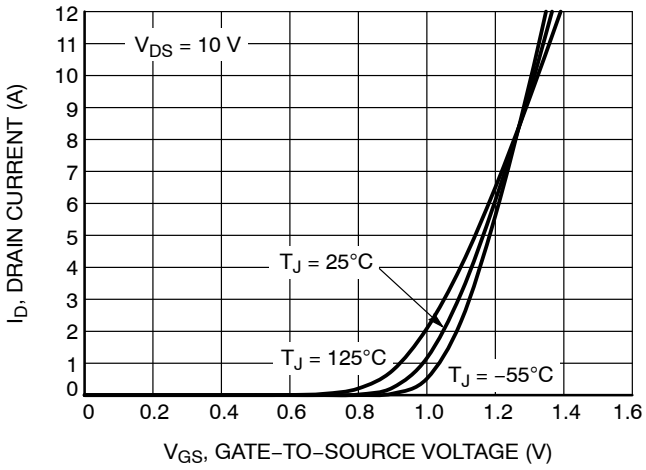


Figure 2. Transfer Characteristics

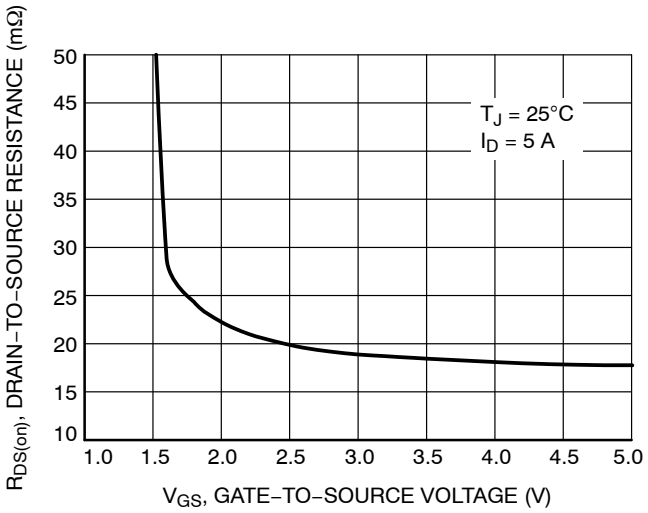


Figure 3. On−Resistance vs. Gate−to−Source Voltage

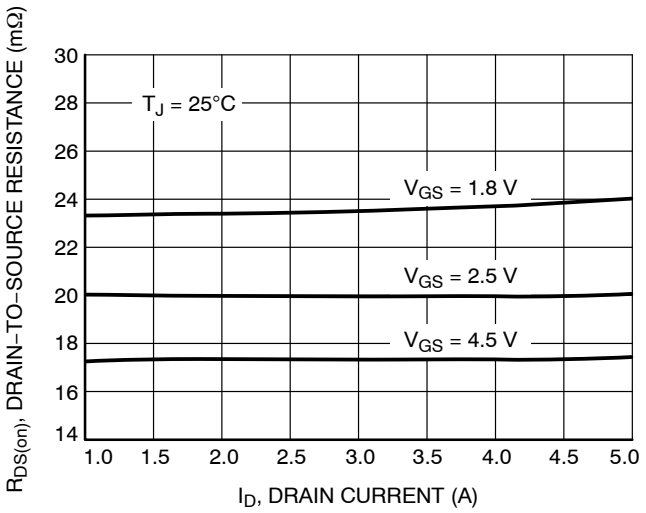


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

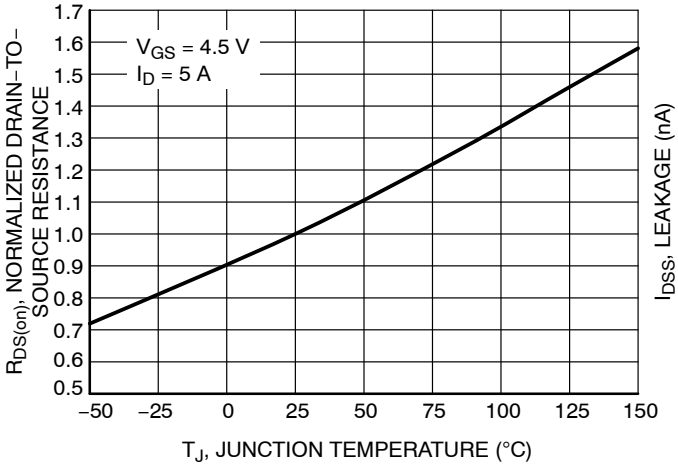


Figure 5. On−Resistance Variation with Temperature

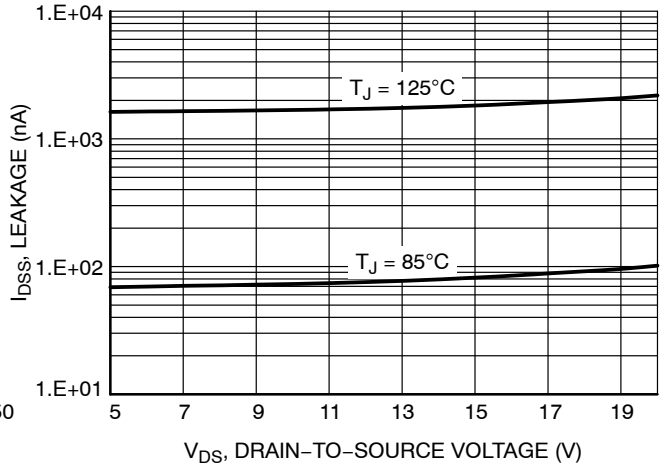


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS (continued)

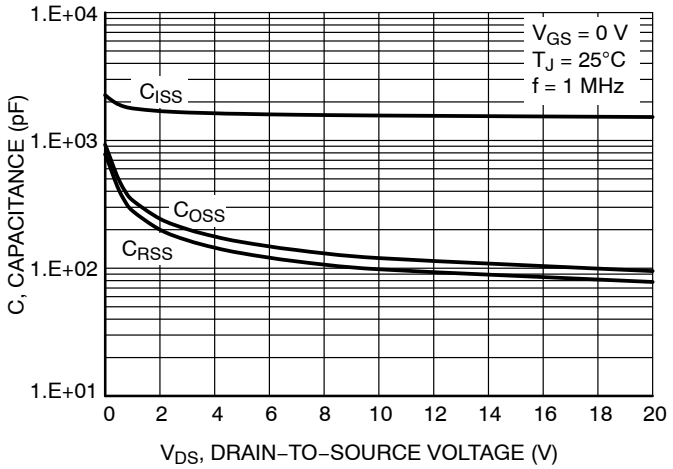


Figure 7. Capacitance Variation

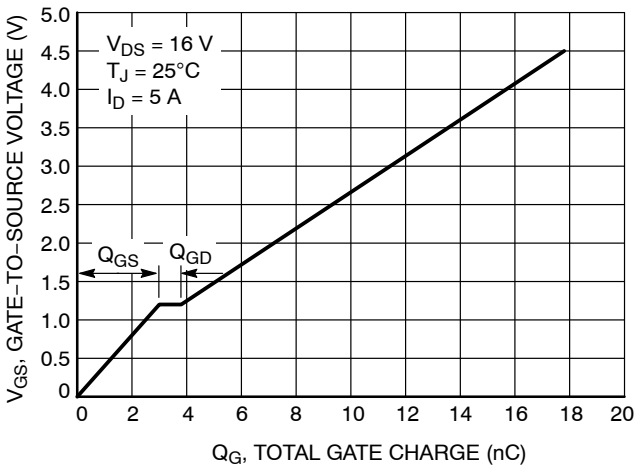


Figure 8. Gate−to−Source vs. Total Charge

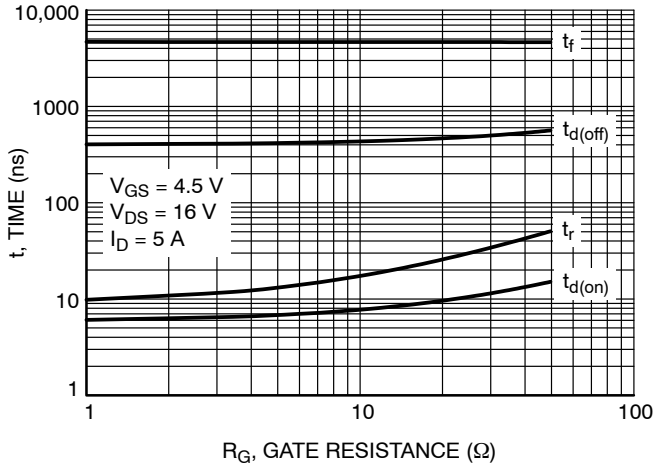


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

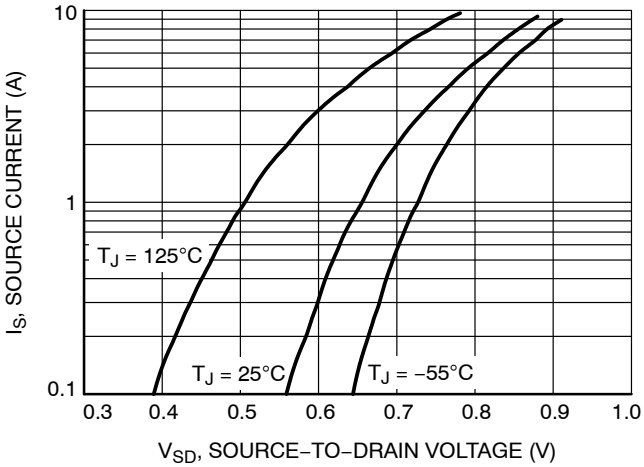


Figure 10. Diode Forward Voltage vs. Current

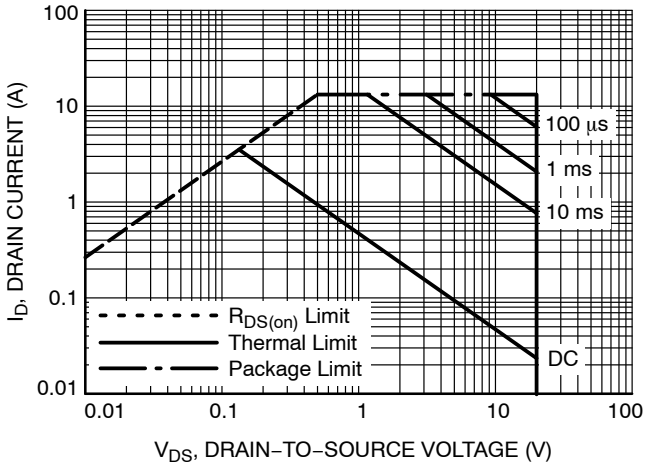


Figure 11. Maximum Rated Forward Biased Safe Operating Area

TYPICAL CHARACTERISTICS (continued)

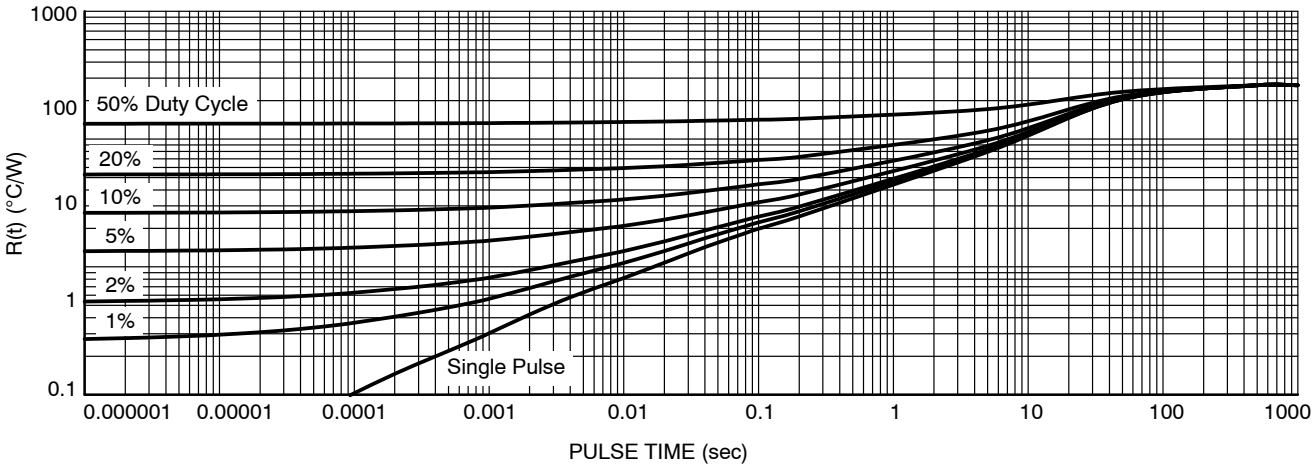
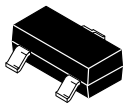


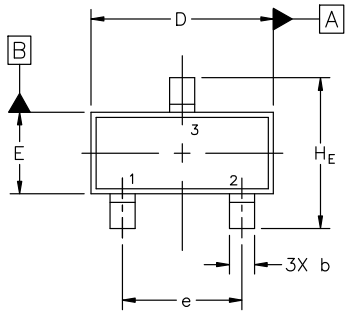
Figure 12. FET Thermal Response



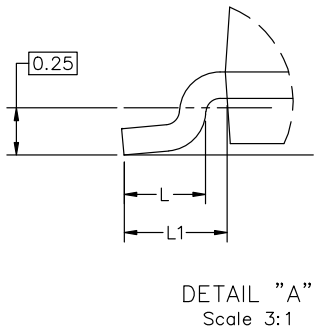
SCALE 4:1

SOT−23 (TO−236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

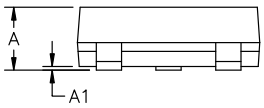
DATE 14 AUG 2024



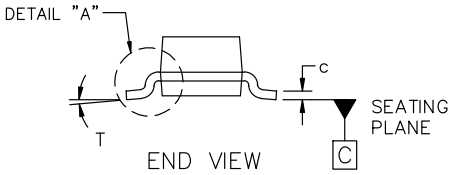
TOP VIEW



DETAIL "A"
Scale 3:1



SIDE VIEW

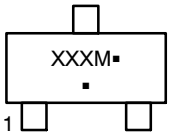


END VIEW

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
H_E	2.10	2.40	2.64
T	0°	−−−	10°

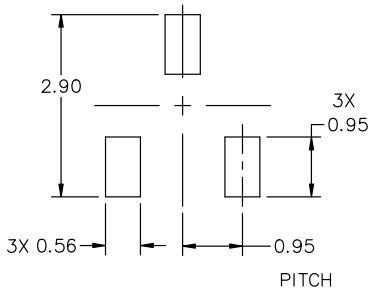
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb−Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

SOT−23 (TO−236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
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onsemi Website: www.onsemi.com

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